



PMV37EN2

30 V, N-channel Trench MOSFET

10 January 2017

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- Enhanced power dissipation capability of 1115 mW

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

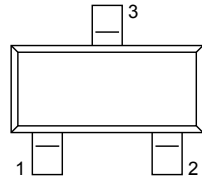
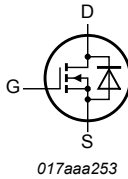
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ }^{\circ}\text{C}$	-	-	30	V
V_{GS}	gate-source voltage		-20	-	20	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}; t \leq 5\text{ s}$	-	-	5.6	A
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 4.5\text{ A}; T_j = 25\text{ }^{\circ}\text{C}$	-	31	36	m Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 TO-236AB (SOT23)	 017aaa253
2	S	source		
3	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV37EN2	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMV37EN2	%K7

[1] % = placeholder for manufacturing site code

8. Limiting values

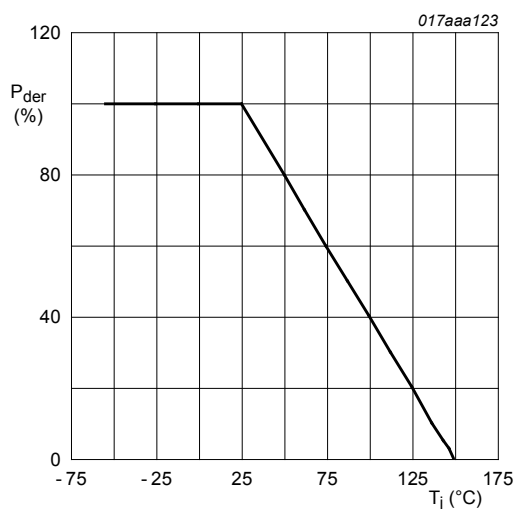
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	5.6	A
		V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	4.5	A
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	2.8	A
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	16	A
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	510	mW
			[1]	-	1115	mW
		T _{sp} = 25 °C		-	5000	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	1	A

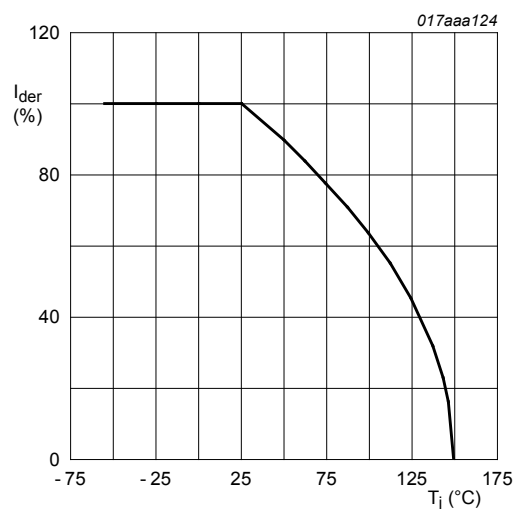
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

[2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



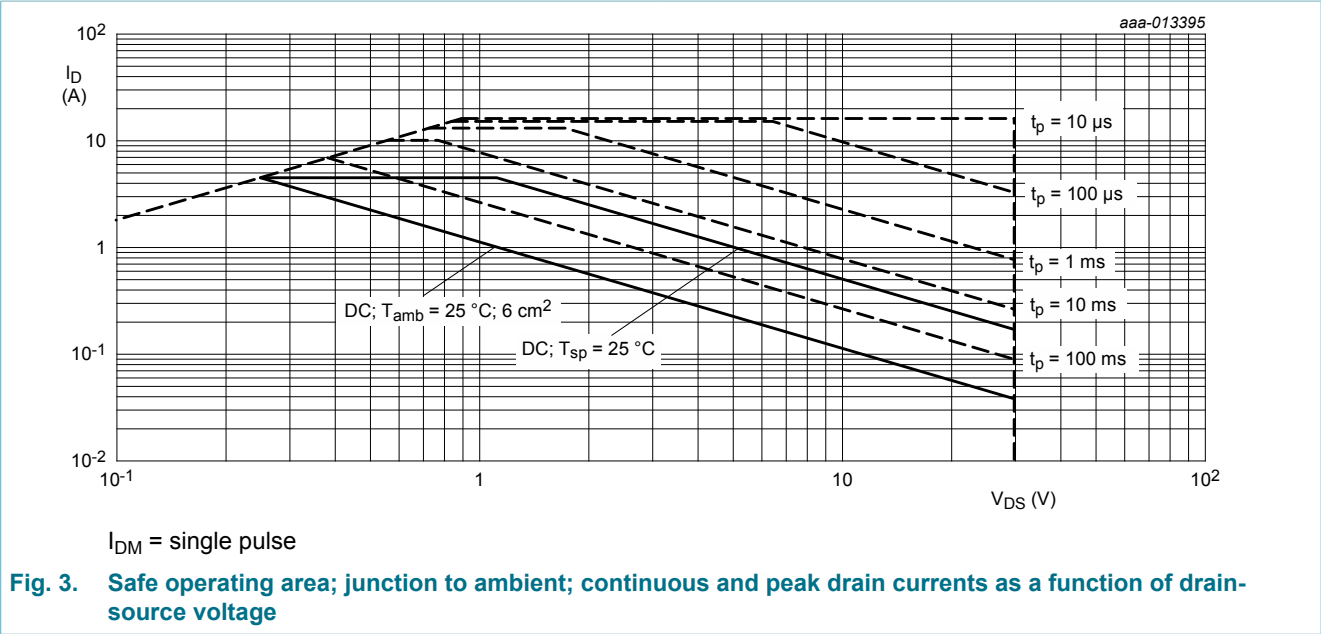
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100 \%$$

Fig. 1. Normalized total power dissipation as a function of junction temperature



$$I_{der} = \frac{I_D}{I_{D(25^\circ C)}} \times 100 \%$$

Fig. 2. Normalized continuous drain current as a function of junction temperature



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	209	246	K/W
			[2]	-	95	112	K/W
		in free air; $t \leq 5\text{ s}$	[2]	-	63	72	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	20	25	K/W

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2 .

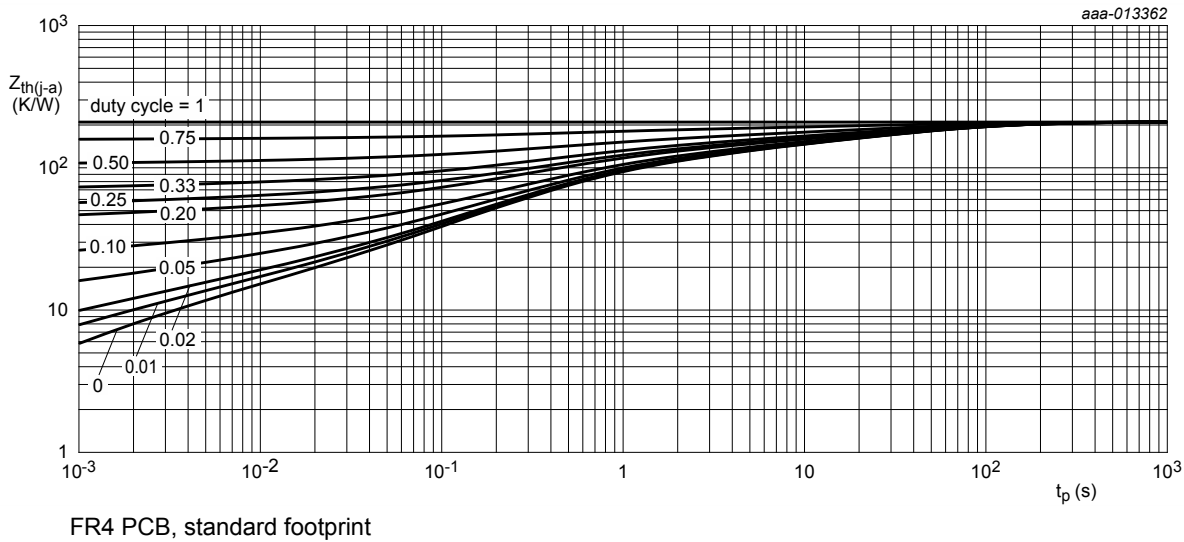


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

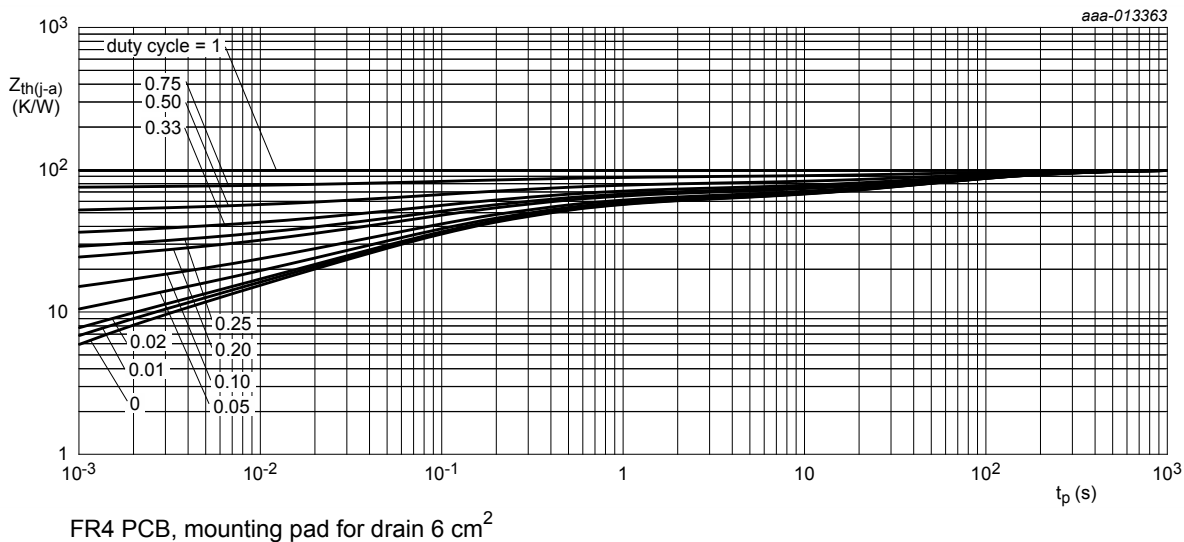


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		30	-	-	V
V _{GSth}	gate-source threshold voltage	I _D = 250 μA; V _{DS} =V _{GS} ; T _j = 25 °C		1	1.5	2	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C		-	-	1	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C		-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C		-	-	-100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 4.5 A; T _j = 25 °C		-	31	36	mΩ
		V _{GS} = 10 V; I _D = 4.5 A; T _j = 150 °C		-	48	56	mΩ
		V _{GS} = 4.5 V; I _D = 3.9 A; T _j = 25 °C		-	37	47	mΩ
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 2 A; T _j = 25 °C		-	13	-	S
R _G	gate resistance	T _j = 25 °C; f = 1 MHz		-	2.3	-	Ω
Dynamic characteristics							
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 3.2 A; V _{GS} = 10 V; T _j = 25 °C		-	3.6	6.3	nC
Q _{GS}	gate-source charge			-	0.5	-	nC
Q _{GD}	gate-drain charge			-	0.4	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; T _j = 25 °C		-	209	-	pF
C _{oss}	output capacitance			-	50	-	pF
C _{rss}	reverse transfer capacitance			-	17	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 3.2 A; V _{GS} = 10 V; R _{G(ext)} = 6 Ω; T _j = 25 °C		-	3	-	ns
t _r	rise time			-	12	-	ns
t _{d(off)}	turn-off delay time			-	11	-	ns
t _f	fall time			-	2	-	ns
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 1 A; V _{GS} = 0 V; T _j = 25 °C		-	0.75	1.2	V

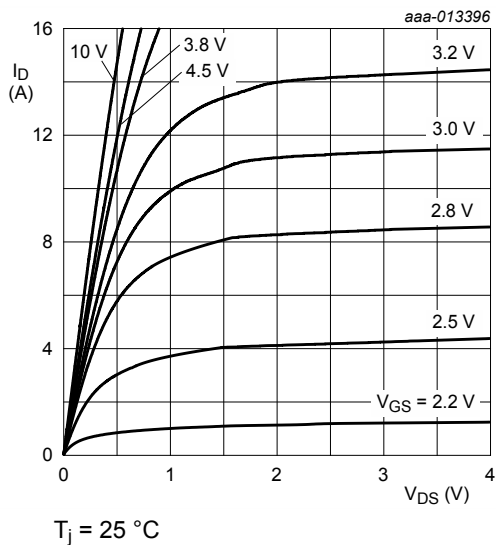


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

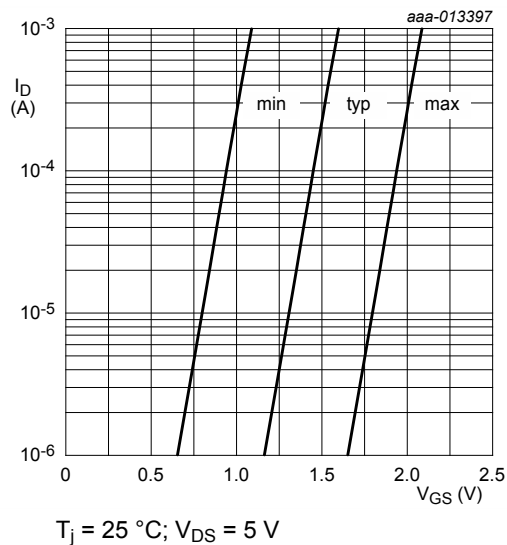


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

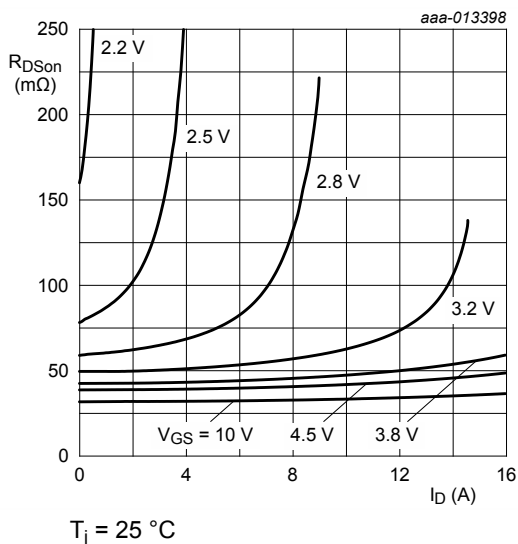


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

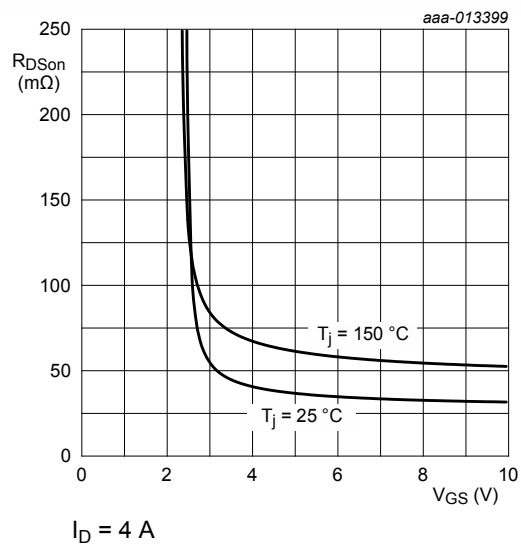


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

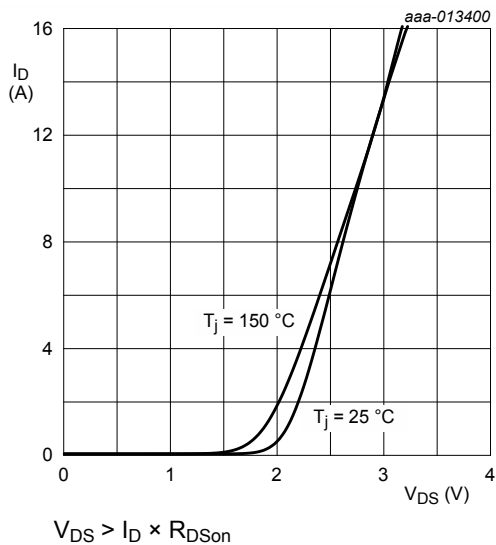


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

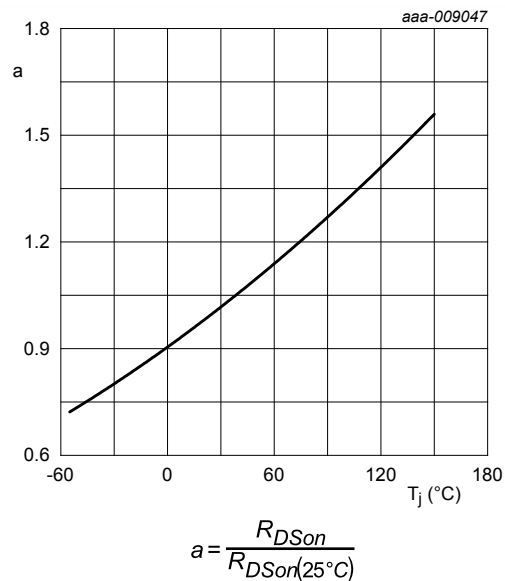


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

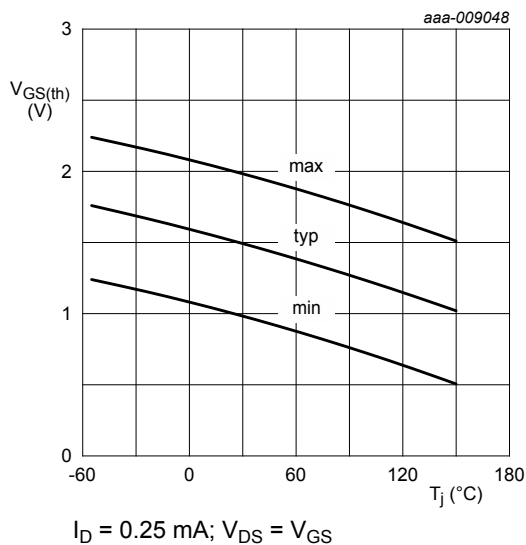


Fig. 12. Gate-source threshold voltage as a function of junction temperature

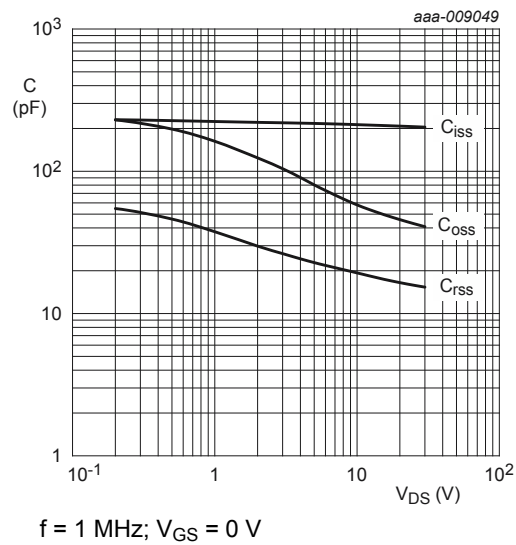


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

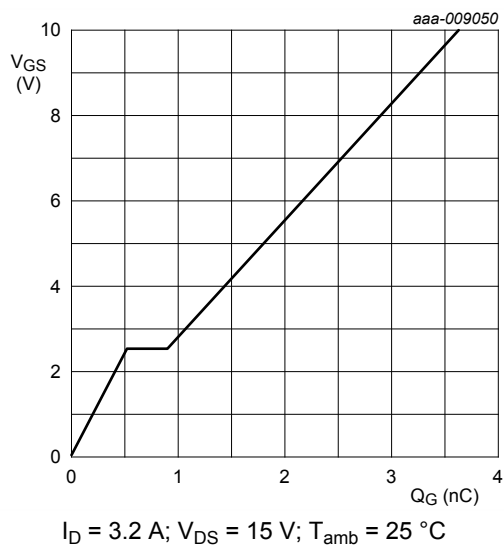


Fig. 14. Gate-source voltage as a function of gate charge; typical values

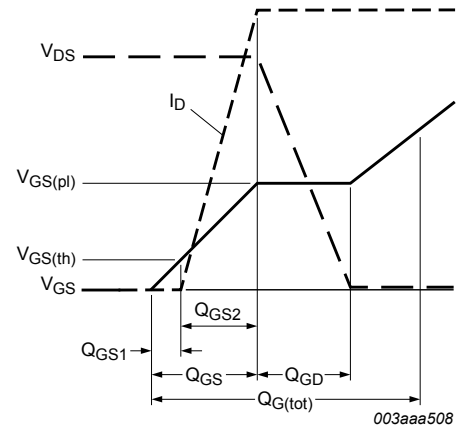


Fig. 15. MOSFET transistor: Gate charge waveform definitions

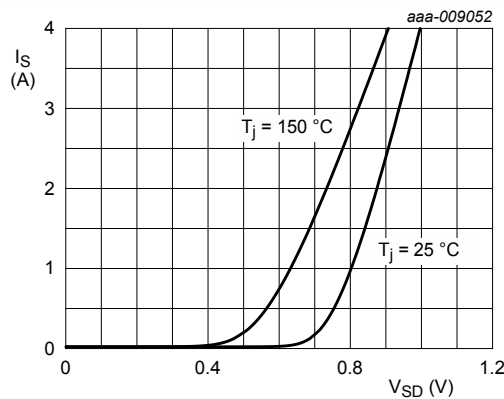


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

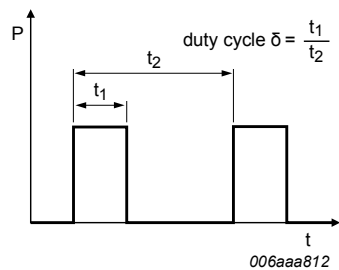


Fig. 17. Duty cycle definition

12. Package outline

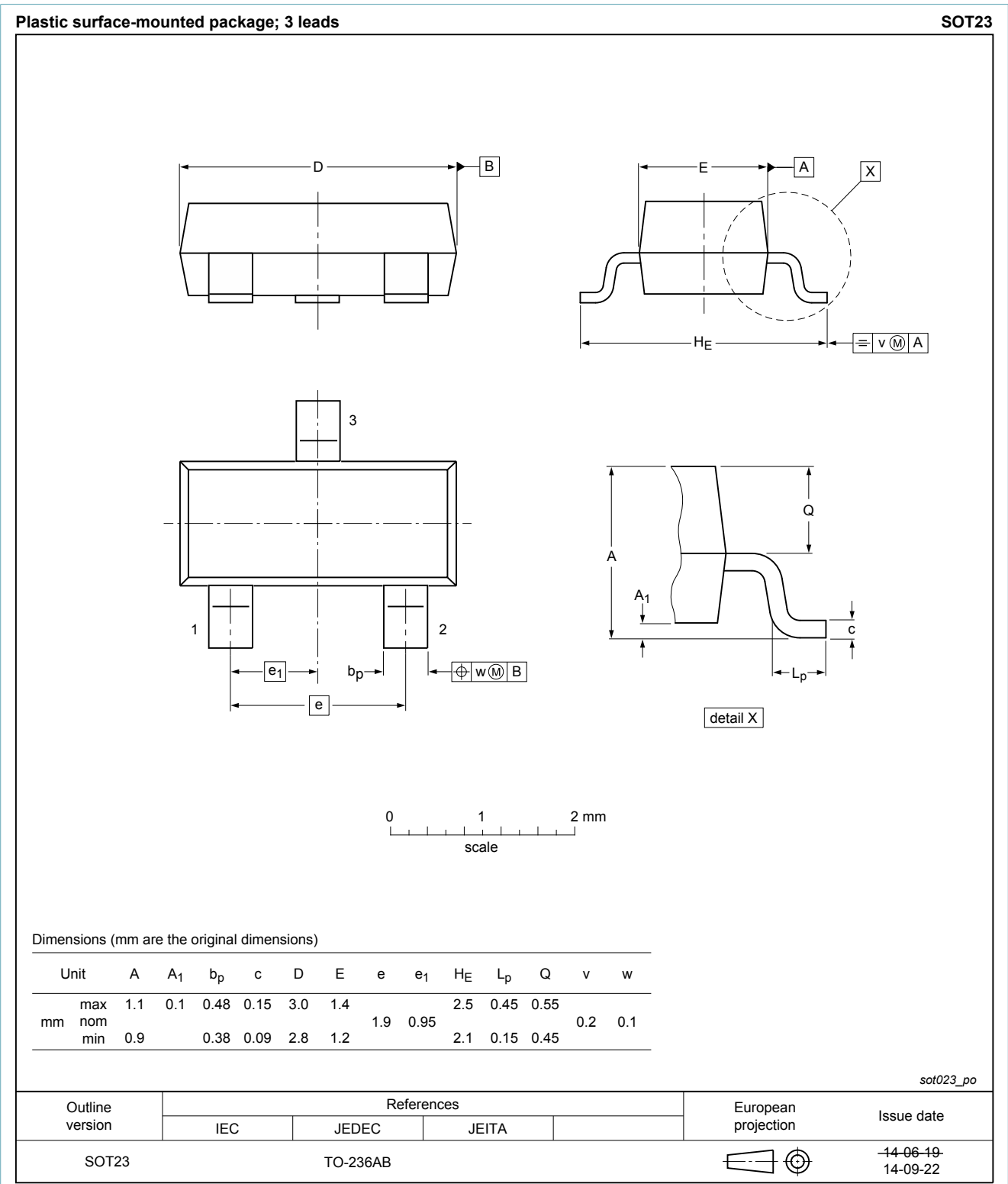


Fig. 18. Package outline TO-236AB (SOT23)

13. Soldering

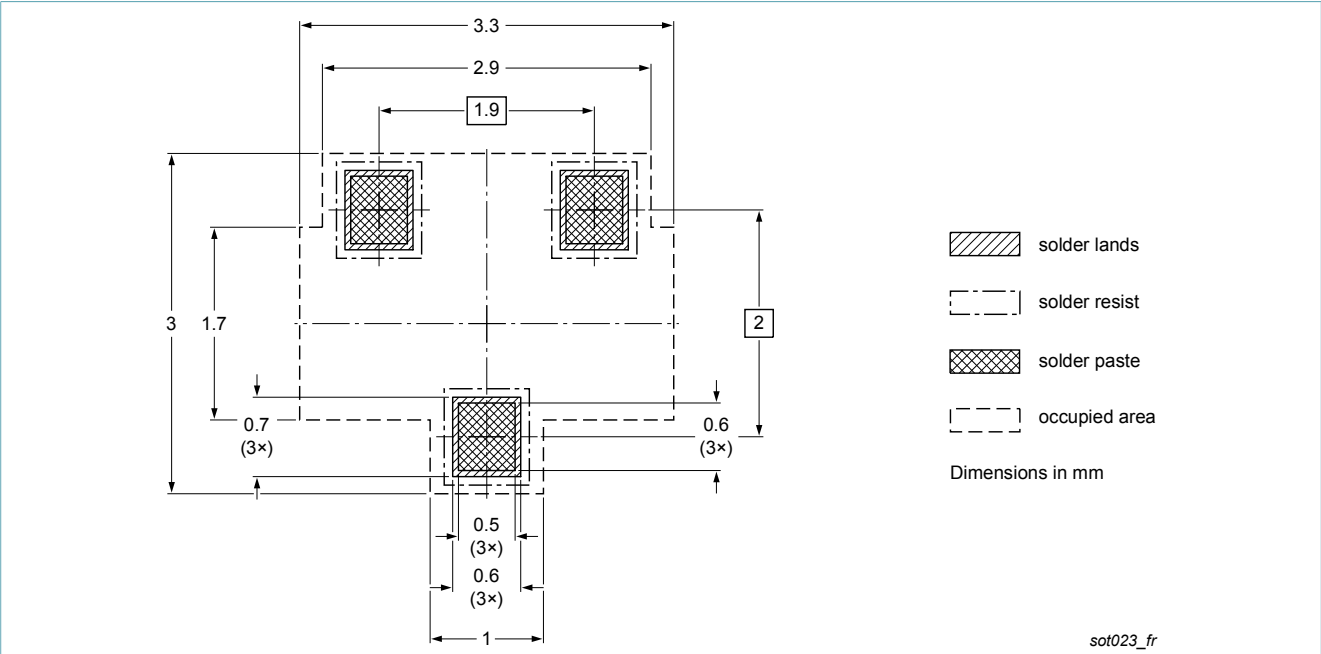


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

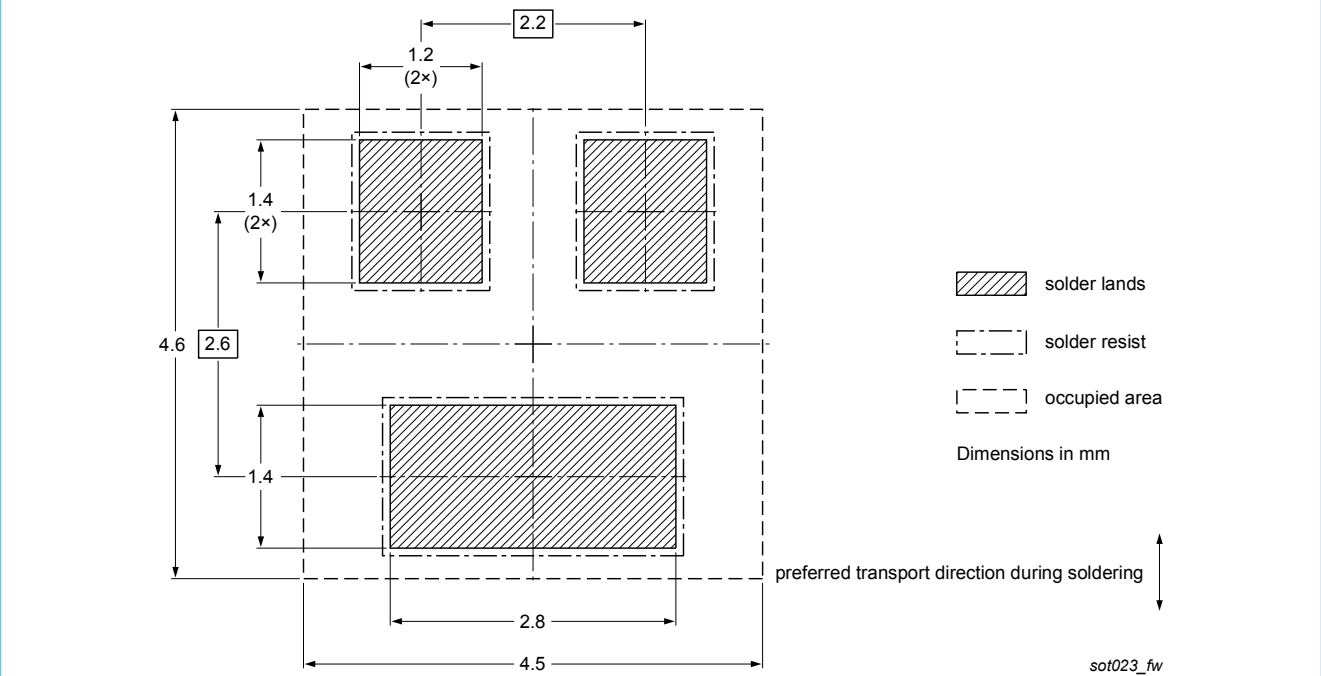


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV37EN2 v.2	20170110	Product data sheet	-	PMV37EN2 v.1
Modifications:	<ul style="list-style-type: none">Section 10. Characteristics: values for forward transconductance and gate resistance changed			
PMV37EN2 v.1	20140603	Product data sheet	-	-

15. Legal information

Data sheet status

Document status ^{[1] [2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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16. Contents

1. General description.....	1
2. Features and benefits.....	1
3. Applications.....	1
4. Quick reference data.....	1
5. Pinning information.....	2
6. Ordering information.....	2
7. Marking.....	2
8. Limiting values.....	3
9. Thermal characteristics.....	4
10. Characteristics.....	6
11. Test information.....	9
12. Package outline.....	10
13. Soldering.....	11
14. Revision history.....	12
15. Legal information.....	13

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